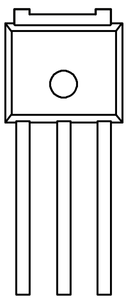
AP9T15J-VB Datasheet

N-Channel 30-V (D-S) MOSFET

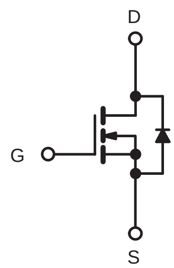
PRODUCT SUMMARY			
V_{DS} (V)	$R_{DS(on)}$ (mΩ)	I_D (A)	Q_g (Typ.)
30	7 at V_{GS} = 10 V	50	19 nC
	9 at V_{GS} = 4.5 V	45	

TO-251



G D S

Top View



N-Channel MOSFET

FEATURES

- **Halogen-free**
- TrenchFET® Gen III Power MOSFET
- 100 % R_g Tested
- 100 % UIS Tested

RoHS COMPLIANT

APPLICATIONS

- DC/DC Conversion
  - System Power

ABSOLUTE MAXIMUM RATINGS T_A = 25 °C, unless otherwise noted

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current (T_J = 150 °C)	T_C = 25 °C	I_D	50	A
	T_C = 70 °C		45	
	T_A = 25 °C		14[b, c]	
	T_A = 70 °C		10[b, c]	
Pulsed Drain Current		I_{DM}	150	
Avalanche Current	L = 0.1 mH	I_{AS}	25	
Avalanche Energy		E_{AS}	40	mJ
Continuous Source-Drain Diode Current	T_C = 25 °C	I_S	15	A
	T_A = 25 °C		2.9[b, c]	
Maximum Power Dissipation	T_C = 25 °C	P_D	28	W
	T_C = 70 °C		18	
	T_A = 25 °C		3.5[b, c]	
	T_A = 70 °C		2.2[b, c]	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150	°C
Soldering Recommendations (Peak Temperature)			260	

THERMAL RESISTANCE RATINGS

Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient	t ≤ 10 s	R_{thJA}	29	36	°C/W
Maximum Junction-to-Case (Drain)	Steady State	R_{thJC}	3.6	4.5	

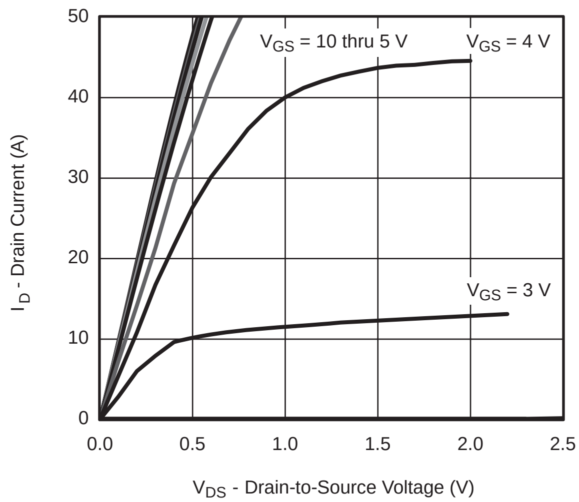
Notes:
a. Based on T_C = 25 °C.
b. Surface Mounted on 1" x 1" FR4 board.
c. t = 10 s.

SPECIFICATIONS T_J = 25 °C, unless otherwise noted						
Parameter	**Symbol**	**Test Conditions**	**Min.**	**Typ.**	**Max.**	**Unit**
Static						
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = 250 µA	30			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	I_D = 250 µA		33		mV/°C
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			- 5		
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS} , I_D = 250 µA	1.2		3.0	V
Gate-Source Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 30 V, V_{GS} = 0 V			1	µA
		V_{DS} = 30 V, V_{GS} = 0 V, T_J = 55 °C			5	
On-State Drain Current[a]	$I_{D(on)}$	$V_{DS} \geq$ 5 V, V_{GS} = 10 V	15			A
Drain-Source On-State Resistance[a]	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 10 A		7		mΩ
		V_{GS} = 4.5 V, I_D = 7 A		9		
Forward Transconductance[a]	g_{fs}	V_{DS} = 15 V, I_D = 10 A		24		S
Dynamic[b]						
Input Capacitance	C_{iss}	V_{DS} = 15 V, V_{GS} = 0 V, f = 1 MHz		1700		pF
Output Capacitance	C_{oss}			200		
Reverse Transfer Capacitance	C_{rss}			150		
Total Gate Charge	Q_g	V_{DS} = 15 V, V_{GS} = 10 V, I_D = 10 A		33		nC
		V_{DS} = 15 V, V_{GS} = 4.5 V, I_D = 10 A		18		
Gate-Source Charge	Q_{gs}			7.3		
Gate-Drain Charge	Q_{gd}			6.2		
Gate Resistance	R_g	f = 1 MHz	0.2	0.8	1.6	Ω
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 15 V, R_L = 1.5 Ω $I_D \cong$ 10 A, V_{GEN} = 4.5 V, R_g = 1 Ω		15	30	ns
Rise Time	t_r			12	24	
Turn-Off Delay Time	$t_{d(off)}$			13	26	
Fall Time	t_f			10	20	
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 15 V, R_L = 1.5 Ω $I_D \cong$ 10 A, V_{GEN} = 10 V, R_g = 1 Ω		9	18	
Rise Time	t_r			9	18	
Turn-Off Delay Time	$t_{d(off)}$			14	28	
Fall Time	t_f			8	16	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	T_C = 25 °C			16	A
Pulse Diode Forward Current	I_{SM}				32	
Body Diode Voltage	V_{SD}	I_S = 3 A, V_{GS} = 0 V		0.78	1.2	V
Body Diode Reverse Recovery Time	t_{rr}	I_F = 10 A, dI/dt = 100 A/µs, T_J = 25 °C		17	34	ns
Body Diode Reverse Recovery Charge	Q_{rr}			9.5	19	nC
Reverse Recovery Fall Time	t_a			10		ns
Reverse Recovery Rise Time	t_b			7		

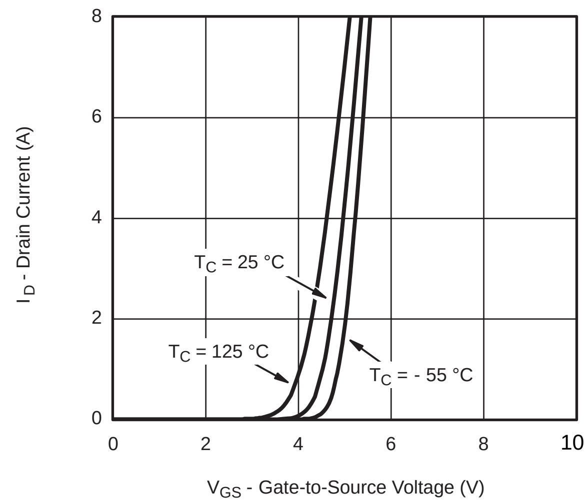
Notes:
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

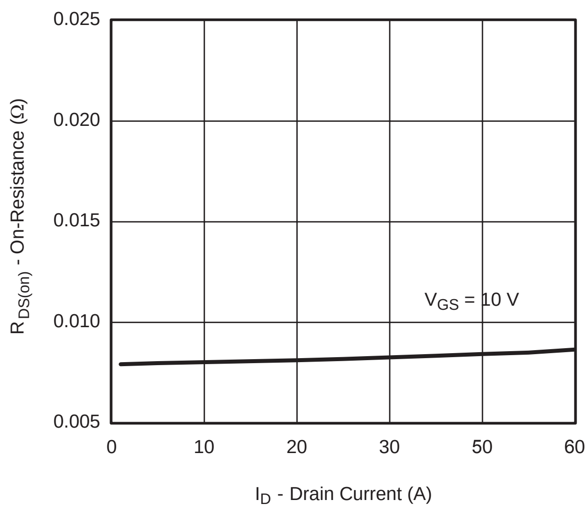
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



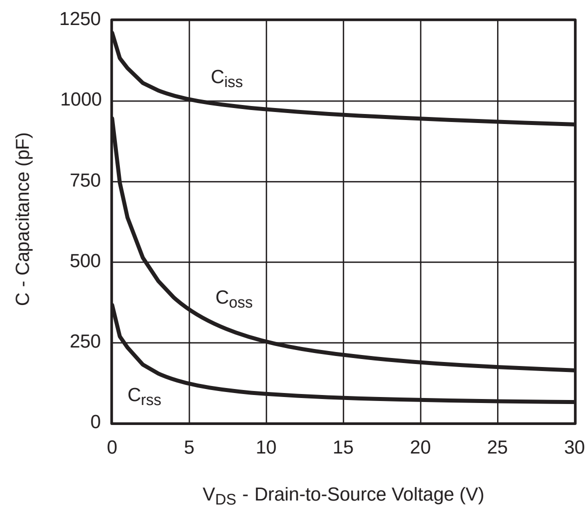
Output Characteristics



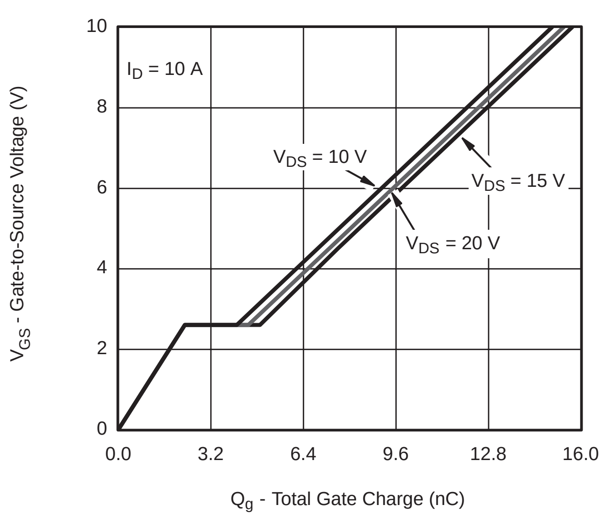
Transfer Characteristics



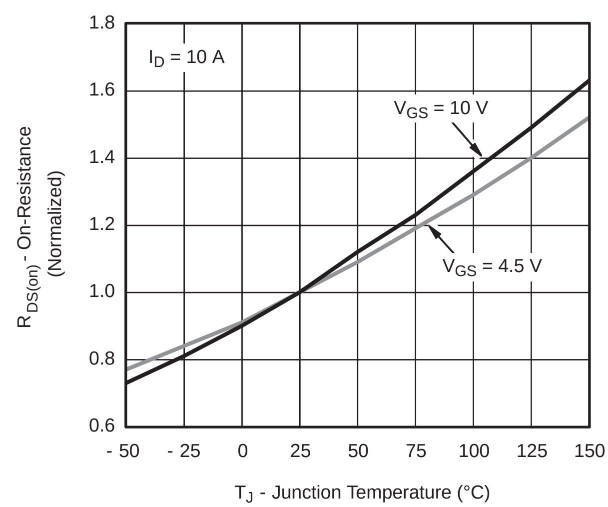
On-Resistance vs. Drain Current and Gate Voltage



Capacitance

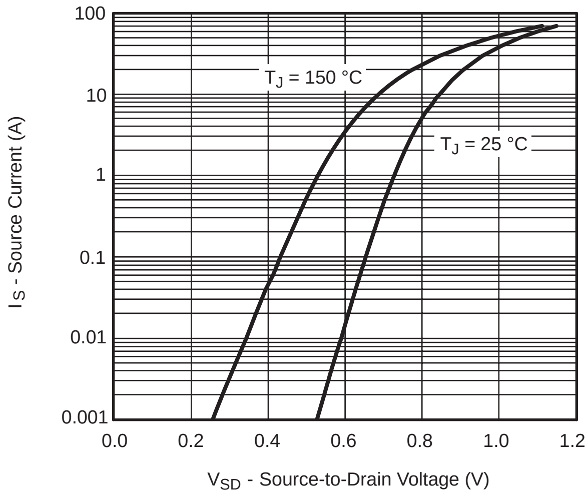


Gate Charge

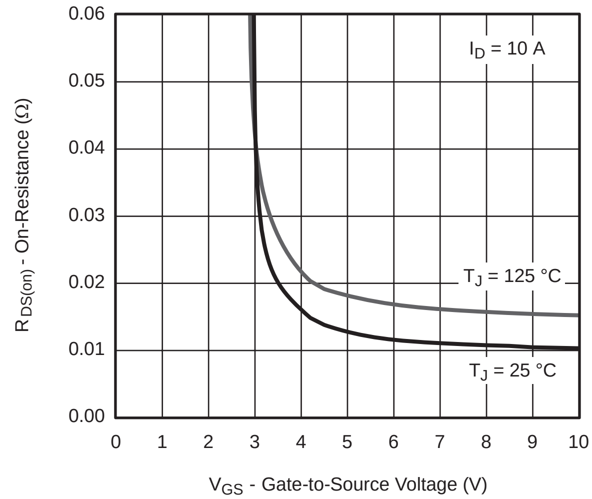


On-Resistance vs. Junction Temperature

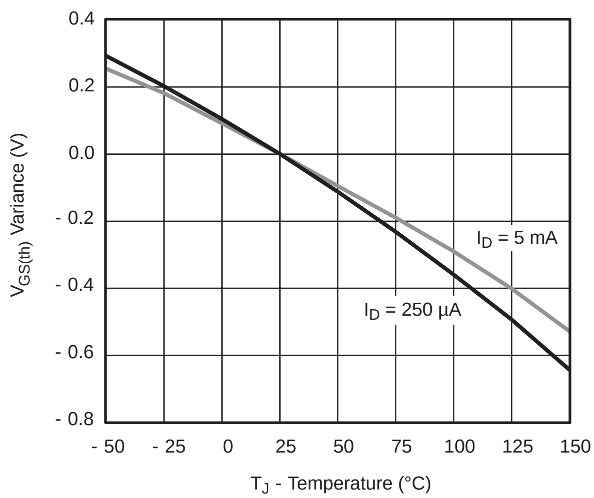
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



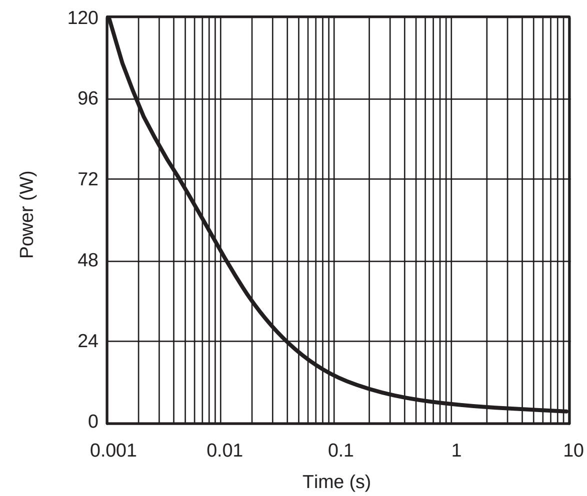
Source-Drain Diode Forward Voltage



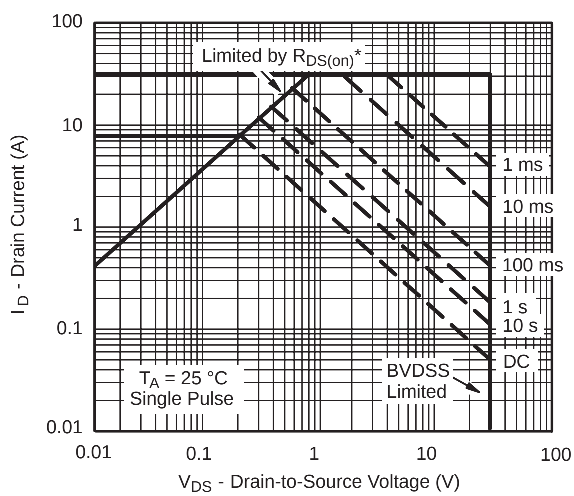
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



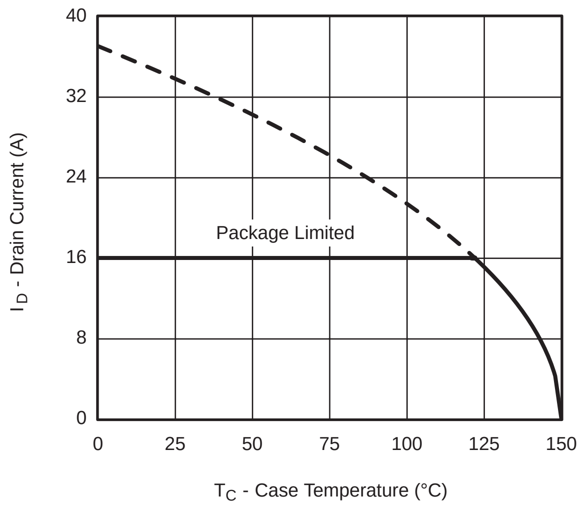
Single Pulse Power (Junction-to-Ambient)



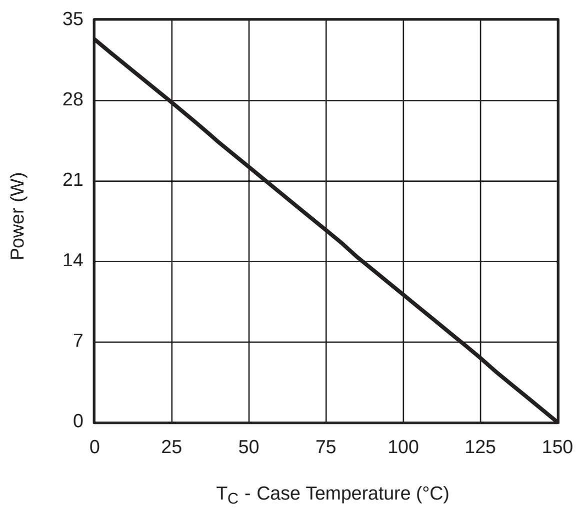
* V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area, Junction-to-Ambient

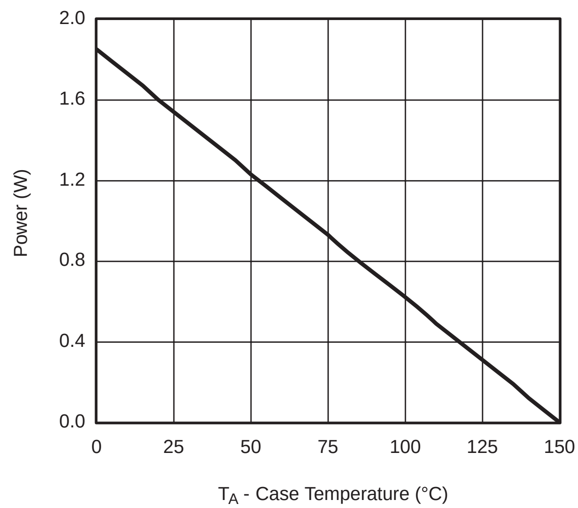
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Current Derating*



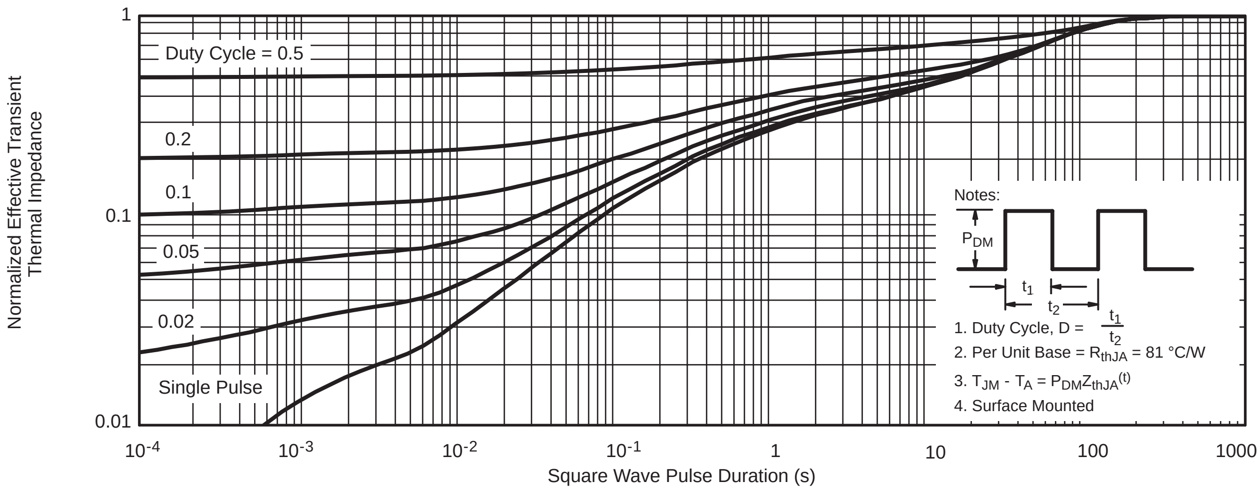
Power, Junction-to-Case



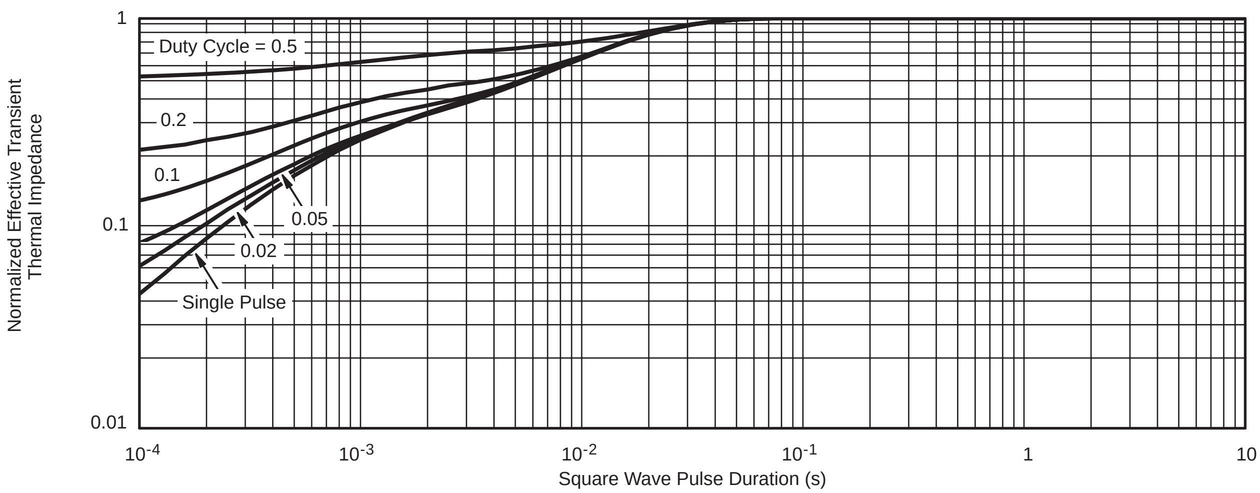
Power, Junction-to-Ambient

* The power dissipation P_D is based on $T_{J(max)}$ = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

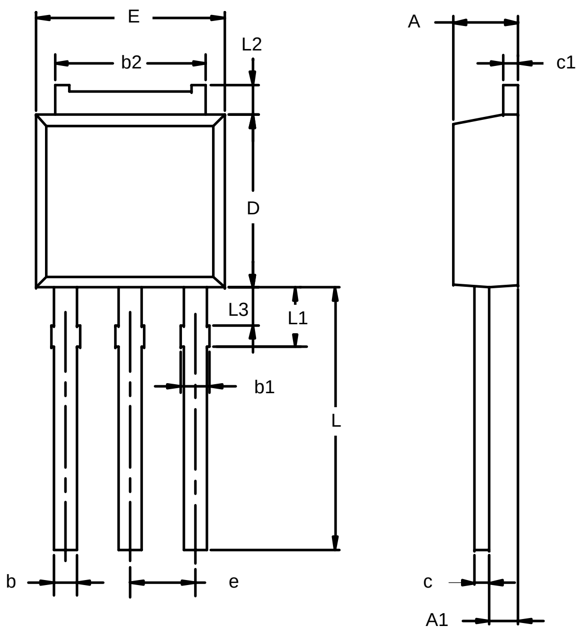


Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

TO-251AA (DPAK)



Note: Dimension L3 is for reference only.

Dim	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	2.21	2.38	0.087	0.094
A1	0.89	1.14	0.035	0.045
b	0.71	0.89	0.028	0.035
b1	0.76	1.14	0.030	0.045
b2	5.23	5.43	0.206	0.214
c	0.46	0.58	0.018	0.023
c1	0.46	0.58	0.018	0.023
D	5.97	6.22	0.235	0.245
E	6.48	6.73	0.255	0.265
e	2.28 BSC		0.090 BSC	
L	3.89	9.53	0.153	0.375
L1	1.91	2.28	0.075	0.090
L2	0.89	1.27	0.035	0.050
L3	1.15	1.52	0.045	0.060

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